

TOSHIBA Transistor Silicon NPN Epitaxial Type

2SC6061

High-Speed Switching Applications
DC-DC Converter Applications

- High-DC current gain: $h_{FE} = 120$ to 300 ($I_C = 0.1$ A)
- Low-collector-emitter saturation: $V_{CE(sat)} = 0.14$ V (max)
- High-speed switching: $t_f = 0.2$ μ s (typ)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	180	V
Collector-emitter voltage		V_{CEX}	150	V
Collector-emitter voltage		V_{CEO}	120	V
Emitter-base voltage		V_{EBO}	7	V
Collector current (Note 1)	DC	I_C	1.0	A
	Pulse	I_{CP}	2.0	A
Base current		I_B	0.1	A
Collector power dissipation (Note 2)	$t = 10$ s	P_C	1000	mW
	DC		625	mW
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55 to 150	$^\circ\text{C}$

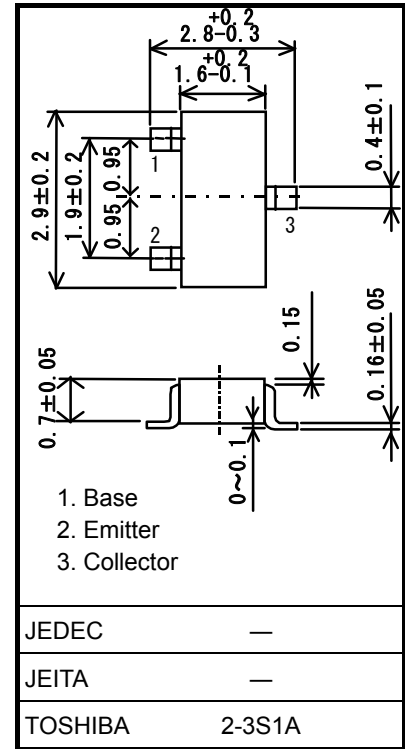
Note 1: Ensure that the channel temperature does not exceed 150°C .

Note 2: Mounted on FR4 board (glass epoxy, 1.6mm thick, Cu area: 645 mm^2)

Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

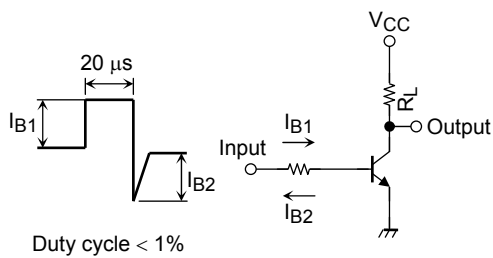


Weight: 0.01g (Typ.)

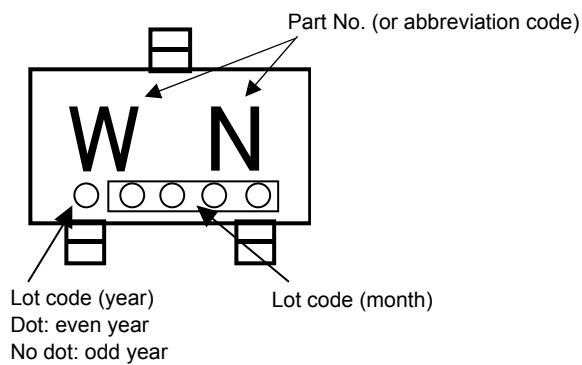
Electrical Characteristics (Ta = 25°C)

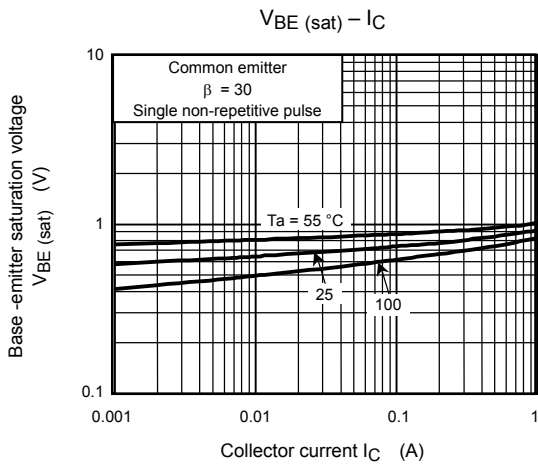
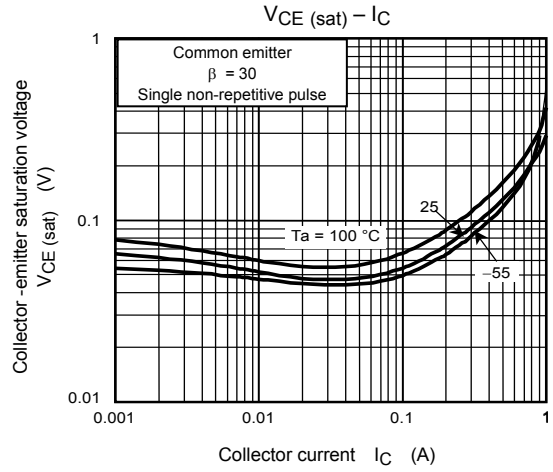
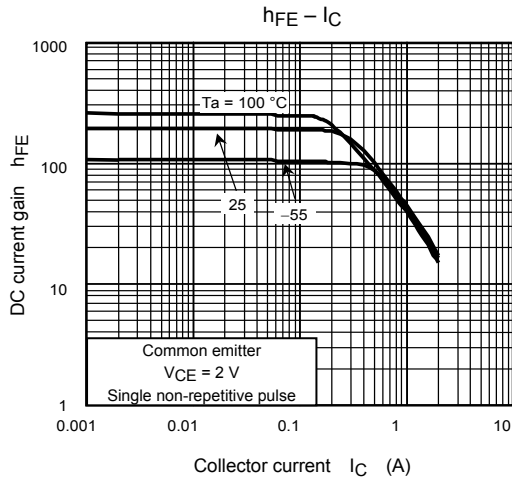
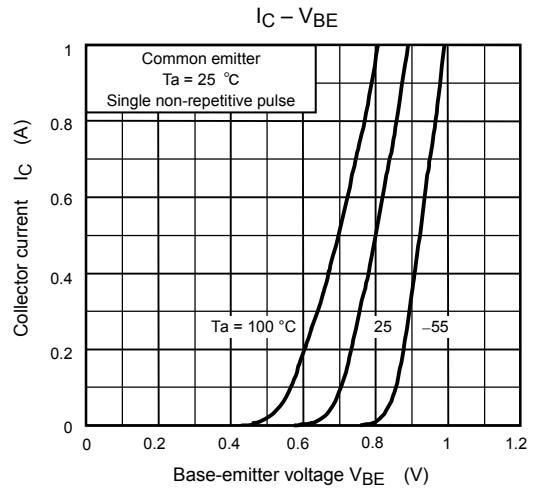
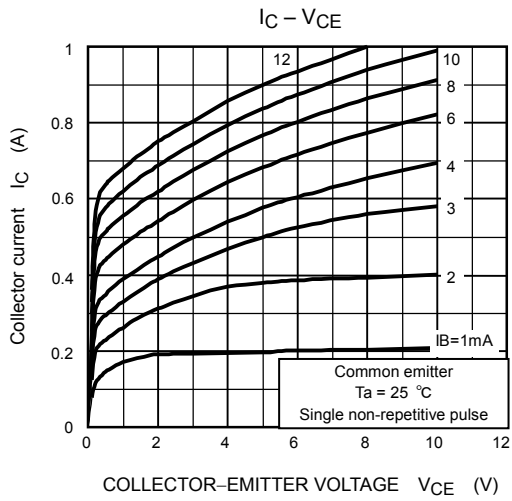
Characteristic	Symbol	Test Conditions	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 180\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	100	nA
Collector-base breakdown voltage	$V_{(BR) CBO}$	$I_C = 1\text{ mA}, I_B = 0$	180	—	—	V
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = 10\text{ mA}, I_B = 0$	120	—	—	V
DC current gain	$h_{FE} (1)$	$V_{CE} = 2\text{ V}, I_C = 1\text{ mA}$	100	—	—	
	$h_{FE} (2)$	$V_{CE} = 2\text{ V}, I_C = 0.1\text{ A}$	120	—	300	
	$h_{FE} (3)$	$V_{CE} = 2\text{ V}, I_C = 0.3\text{ A}$	60	—	—	
Collector emitter saturation voltage	$V_{CE (sat)}$	$I_C = 0.3\text{ A}, I_B = 0.01\text{ A}$	—	—	0.14	V
Base-emitter saturation voltage	$V_{BE (sat)}$	$I_C = 0.3\text{ A}, I_B = 0.01\text{ A}$	—	—	1.1	V
Switching time	Rise time	t_r	See Figure 3 circuit diagram		—	μs
	Storage time	t_{stg}	—	0.1	—	
	Fall time	t_f	—	1.5	—	
			—	0.2	—	

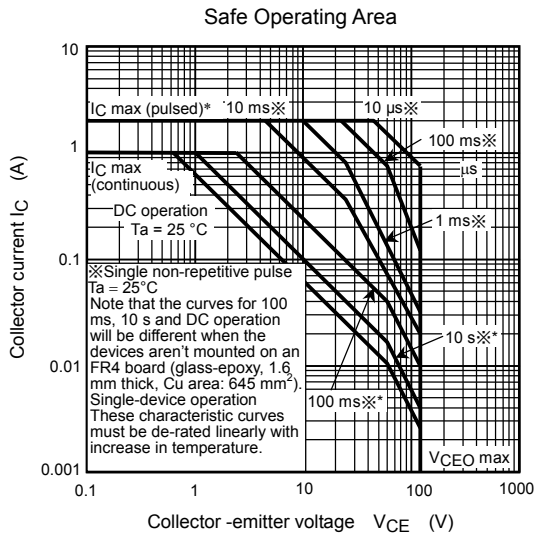
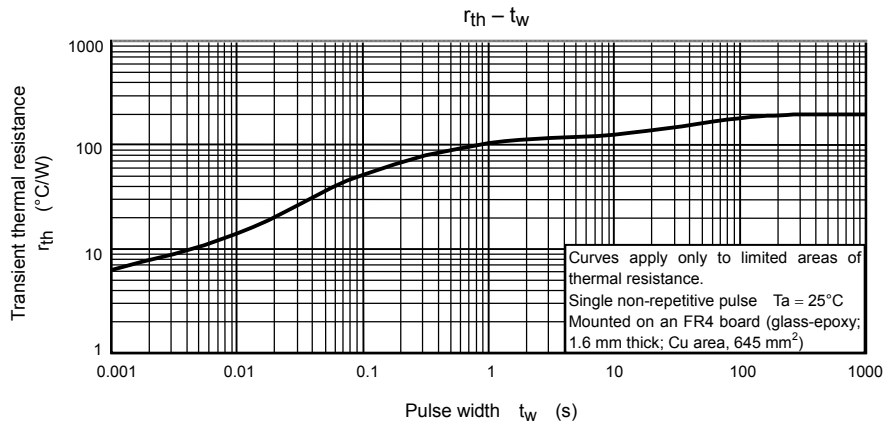
Figure 3 Switching Time Test Circuit & Timing Chart



Marking







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